



JMSH1504ATL

150V 3.3mΩ TOLL N-Ch Power MOSFET

Features

- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

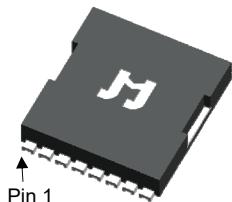
Product Summary

Parameter	Value	Unit
V_{DS}	150	V
$V_{GS(th)}_{Typ}$	3.2	V
$I_D (@ V_{GS} = 10V)$ ⁽¹⁾	263	A
$R_{DS(ON)}_{Typ} (@ V_{GS} = 10V)$	3.3	mΩ

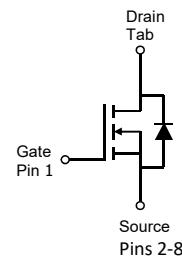
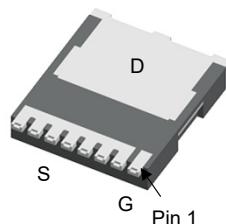
Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Motor Driving in Power Tool, E-vehicle, Robotics

PowerJE®10x12 Top



PowerJE®10x12 Bottom



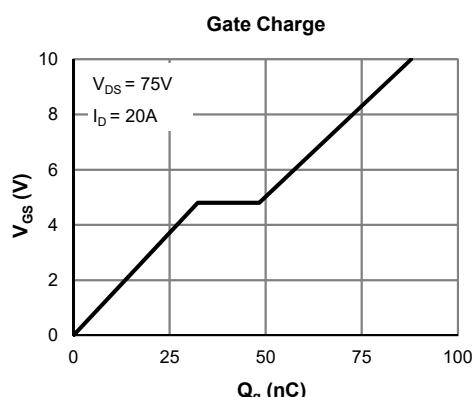
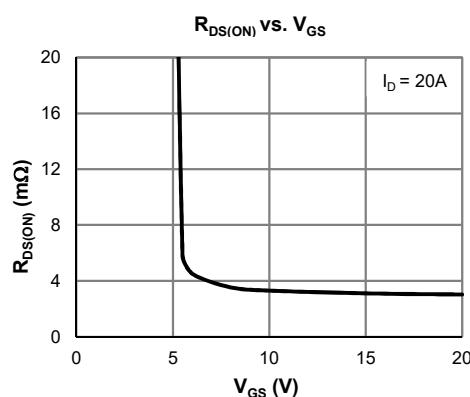
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1504ATL-13	PowerJE®10x12 ⁽¹⁾	8	SH1504A	1	-55 to 175	13-inch Reel	2000

Note 1: PowerJE® is a registered trademark of JieJie Micro., its package outline is compatible to that of TO-LeadLess (TOLL).

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	150	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁽²⁾	I_D	263	A
$T_C = 100^\circ\text{C}$		186	
Pulsed Drain Current ⁽³⁾	I_{DM}	817	A
Avalanche Current ⁽⁴⁾	I_{AS}	49	A
Avalanche Energy ⁽⁴⁾	E_{AS}	1201	mJ
Power Dissipation ⁽⁵⁾	P_D	600	W
$T_C = 100^\circ\text{C}$		300	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C



**Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	150			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0	μA
					5.0	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.2	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(\text{ON})}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		3.3	4.2	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		65		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.71	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			600	A
DYNAMIC PARAMETERS (6)						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 75\text{V}, f = 1\text{MHz}$		6540		pF
Output Capacitance	C_{oss}			772		pF
Reverse Transfer Capacitance	C_{rss}			6.7		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.4		Ω
SWITCHING PARAMETERS (6)						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 75\text{V}, I_D = 20\text{A}$		88		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			57		nC
Gate Source Charge	Q_{gs}			32		nC
Gate Drain Charge	Q_{gd}			16		nC
Turn-On DelayTime	$t_{D(\text{on})}$	$V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$ $R_L = 3.75\Omega, R_{\text{GEN}} = 6\Omega$		48		ns
Turn-On Rise Time	t_r			90		ns
Turn-Off DelayTime	$t_{D(\text{off})}$			94		ns
Turn-Off Fall Time	t_f			60		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	122		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		279		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	55	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.20	0.25	$^\circ\text{C/W}$

Notes:

2. Computed continuous current assumes the condition of $T_{J_{\text{Max}}}$ while the actual continuous current depends on the thermal & electro-mechanical application board design.
3. This single-pulse measurement was taken under $T_{J_{\text{Max}}} = 175^\circ\text{C}$.
4. This single-pulse measurement was taken under the following condition [$L = 1\text{mH}, V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$] while its value is limited by $T_{J_{\text{Max}}} = 175^\circ\text{C}$.
5. The power dissipation P_D is based on $T_{J_{\text{Max}}} = 175^\circ\text{C}$.
6. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

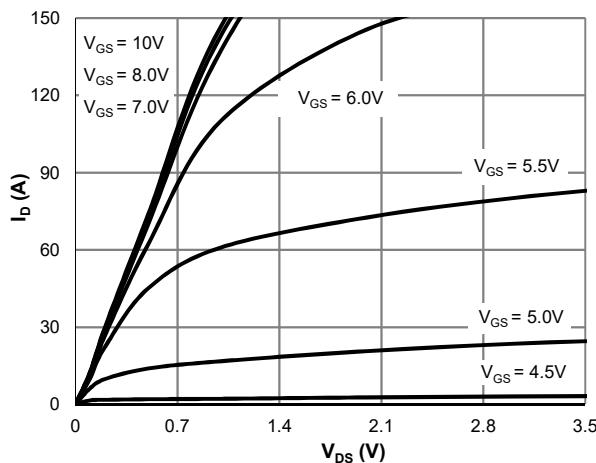


Figure 1: Saturation Characteristics

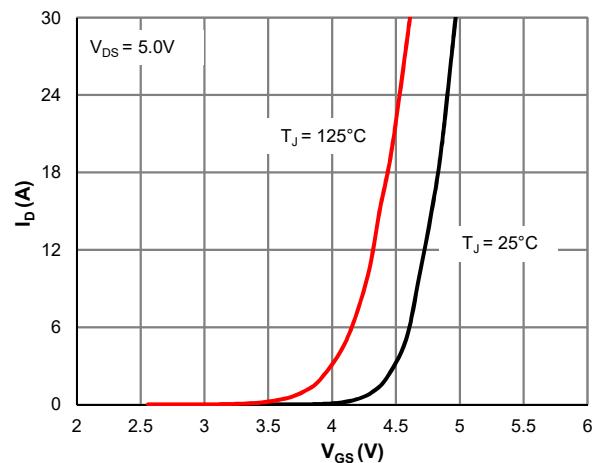


Figure 2: Transfer Characteristics

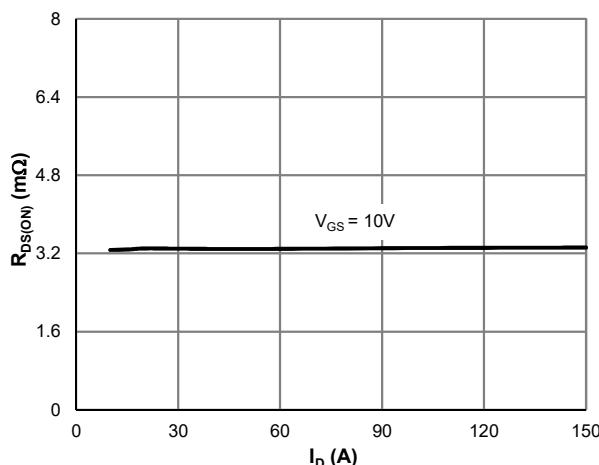


Figure 3: $R_{DS(ON)}$ vs. Drain Current

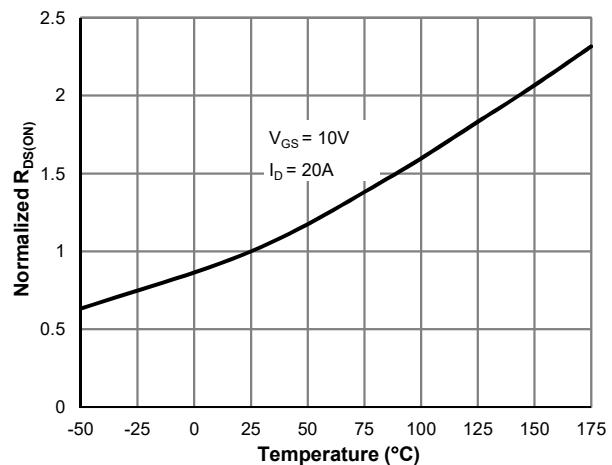


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

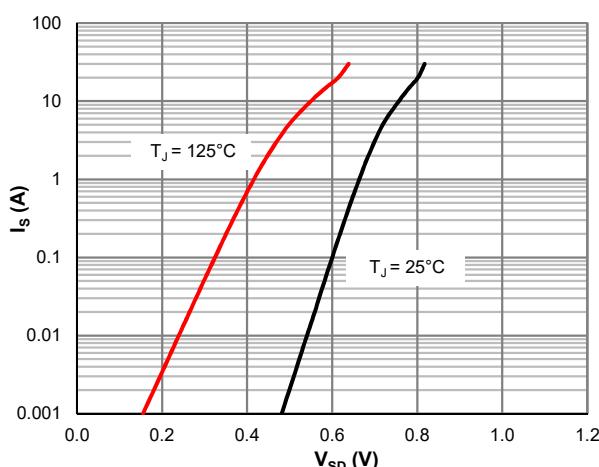


Figure 5: Body-Diode Characteristics

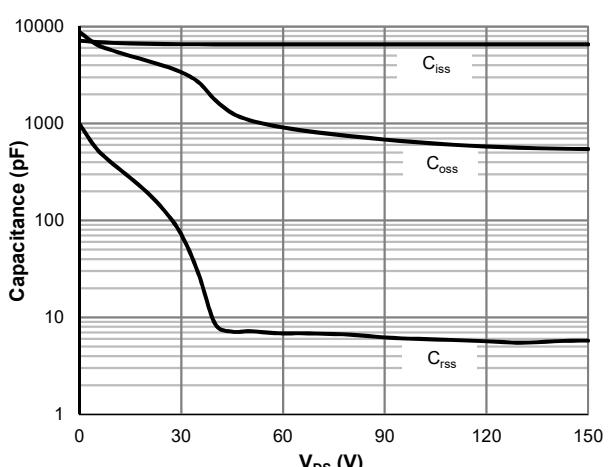


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

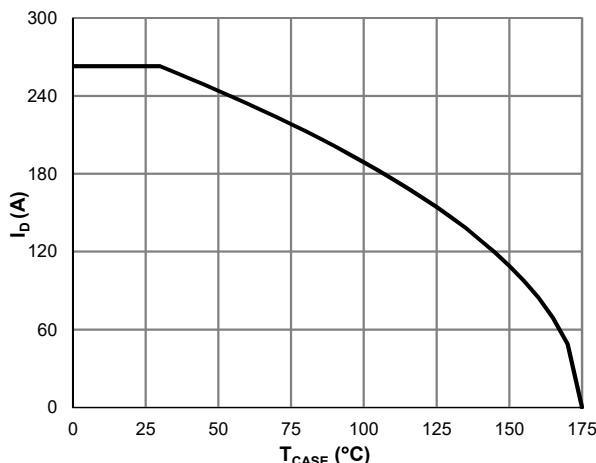


Figure 7: Current De-rating

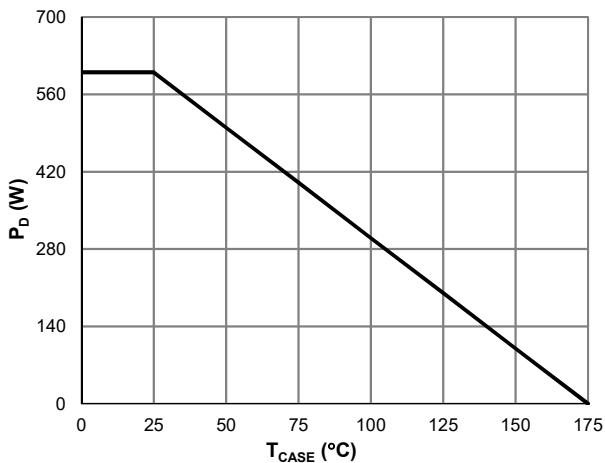


Figure 8: Power De-rating

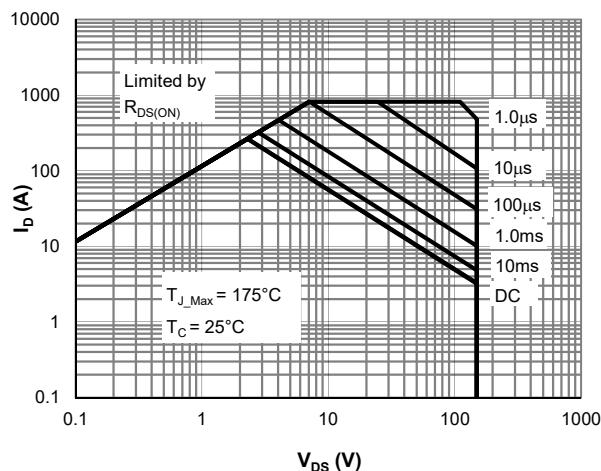


Figure 9: Maximum Safe Operating Area

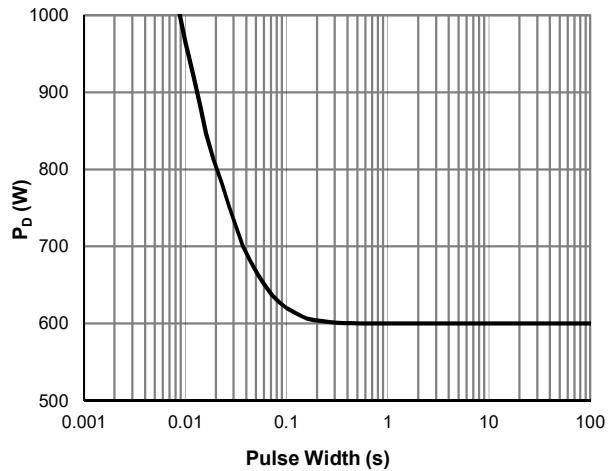


Figure 10: Single Pulse Power Rating, Junction-to-Case

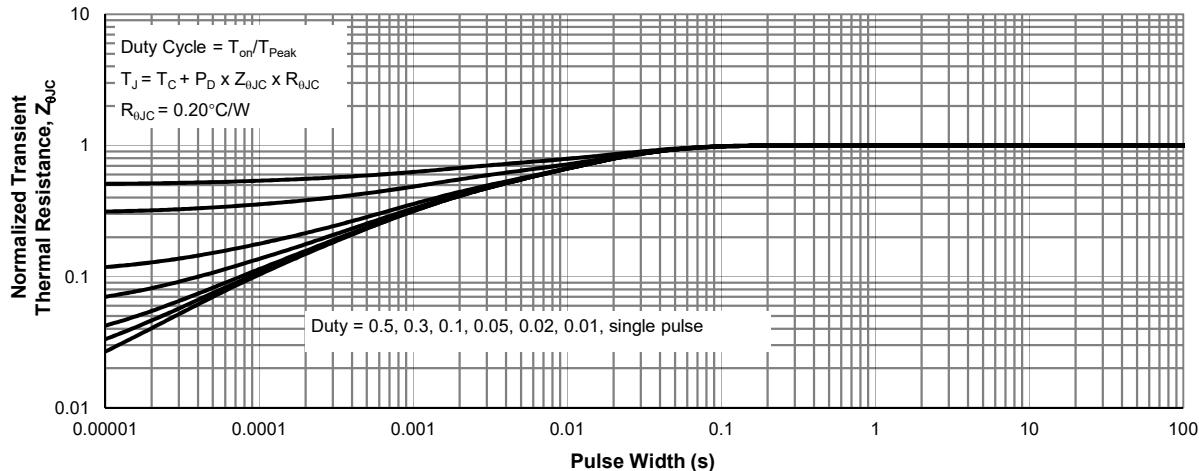
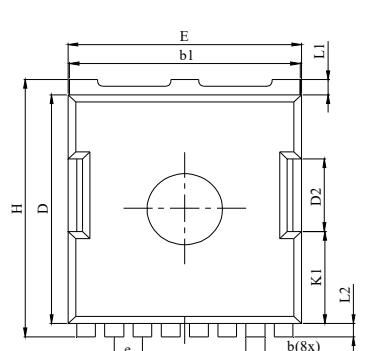
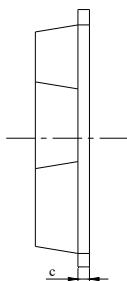


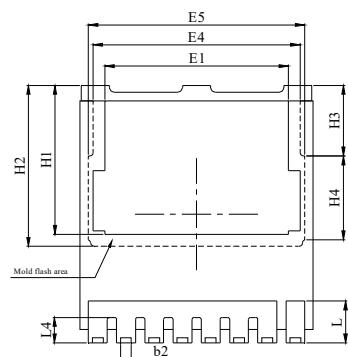
Figure 11: Normalized Maximum Transient Thermal Impedance

PowerJE®10x12 Package Information
Package Outlines


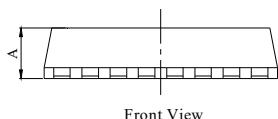
Top View



Side View



Bottom View



Front View

NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
c	0.40	0.50	0.60
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e		1.20 (BSC)	
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2		7.30	
H3		3.20	
H4		3.80	
K1		4.18	
L	1.70	1.90	2.10
L1		0.70	
L2		0.60	
L4	1.00	1.15	1.30

Recommended Soldering Footprint
